Elektronische Bauelemente

2SA1179

-0.15A , -55V

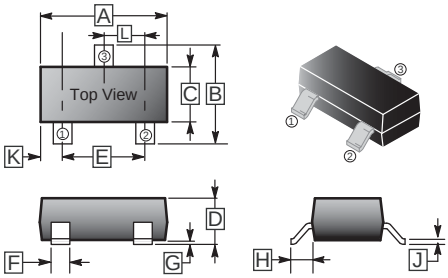
PNP Silicon Plastic Encapsulated Transistor

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

SOT-23

FEATURES

- High breakdown voltage



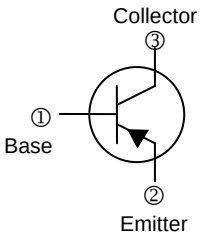
MARKING

Product	Marking Code
2SA1179	M

PACKAGE INFORMATION

Package	MPQ	LeaderSize
SOT-23	3K	7' inch

REF.	Millimeter Min.	Millimeter Max.	REF.	Millimeter Min.	Millimeter Max.
A	2.80	3.00	G	0.10 REF.	
B	2.25	2.55	H	0.55 REF.	
C	1.20	1.40	J	0.08	0.15
D	0.90	1.15	K	0.5 REF.	
E	1.80	2.00	L	0.95 TYP.	
F	0.30	0.50			



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	-55	V
Collector to Emitter Voltage	V_{CEO}	-50	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-150	mA
Collector Power Dissipation	P_C	200	mW
Junction and Storage Temperature	T_J, T_{STG}	150, -55~150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	-55	-	-	V	I_C= -10μA, I_E=0
Collector to Emitter Breakdown	$V_{(BR)CEO}$	-50	-	-	V	I_C= -1mA, I_B=0
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	-5	-	-	V	I_E= -10μA, I_C=0
Collector Cut-off Current	I_{CBO}	-	-	-0.1	μA	V_{CB}= -35V, I_E=0
Emitter Cut-off Current	I_{EBO}	-	-	-0.1	μA	V_{EB}= -4V, I_C=0
DC Current Gain	h_{FE}	200	-	400		V_{CE}= -6V, I_C= -1mA
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	-	-	-0.5	V	I_C= -50mA, I_B= -5mA
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	-	-	-1.0	V	I_C= -50mA, I_B= -5mA
Transition Frequency	f_T	-	180	-	MHz	V_{CE}= -6V, I_C= -10mA
Collector Output Capacitance	C_{ob}	-	4	-	pF	V_{CB}= -6V, I_E=0, f=1MHz

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CHARACTERISTICS CURVE

